CMOS STATIC RAM 256K (32K x 8-BIT)

FEATURES:

- 32K x 8 advanced high-speed CMOS static RAM
- Commercial (0° to 70°C) and Industrial (-40° to 85°C) temperature options
- · Equal access and cycle times
 - Commercial: 12/15/20/25ns
 - Industrial: 15/20ns
- · One Chip Select plus one Output Enable pin
- Bidirectional data inputs and outputs directly TTL-compatible
- · Low power consumption via chip deselect
- Commercial product available in 28-pin 300- and 600-mil Plastic DIP, 300 mil Plastic SOJ and TSOP packages
- Industrial product available in 28-pin 300 mil Plastic SOJ and TSOP packages

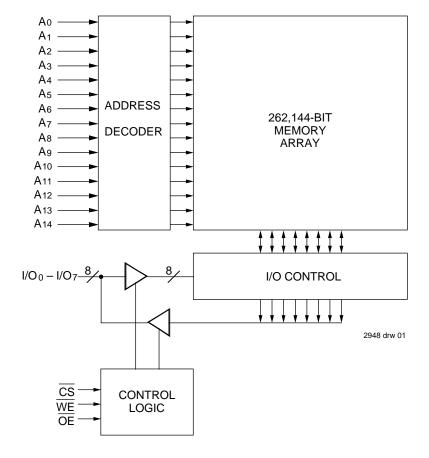
DESCRIPTION:

The ID71256SA is a 262,144-bit high-speed Static RAM organized as 32K x 8. It is fabricated using IDT's high-perfomance, high-reliability CMOS technology. This state-of-the-art technology, combined with innovative circuit design techniques, provides a cost-effective solution for high-speed memory needs.

The IDT71256SA has an output enable pin which operates as fast as 6ns, with address access times as fast as 12ns. All bidirectional inputs and outputs of the IDT71256SA are TTL-compatible and operation is from a single 5V supply. Fully static asynchronous circuitry is used, requiring no clocks or refresh for operation.

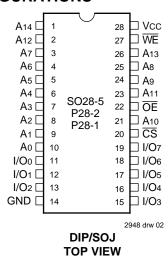
The IDT71256SA is packaged in 28-pin 300- and 600-mil Plastic DIP, 28-pin 300 mil Plastic SOJ and TSOP.

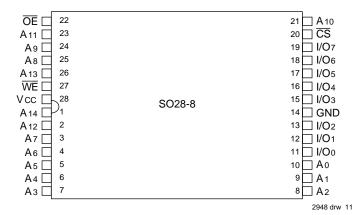
FUNCTIONAL BLOCK DIAGRAM



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PIN CONFIGURATIONS





TSOP TOP VIEW

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Value	Unit
Vcc	Supply Voltage Relative to GND	-0.5 to +7.0	V
VTERM	Terminal Voltage Relative to GND	-0.5 to Vcc+0.5	V
TBIAS	Temperature Under Bias	-55 to +125	°C
Tstg	Storage Temperature	-55 to +125	°C
Рт	Power Dissipation	1.0	W
Іоит	DC Output Current	50	mA

NOTES:

2948 tbl 02

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

TRUTH TABLE(1,2)

<u>cs</u>	ŌĒ	WE	I/O	Function
L	L	Н	DATAout	Read Data
L	Х	L	DATAIN	Write Data
L	Н	Н	High-Z	Outputs Disabled
Н	Х	Х	High-Z	Deselected — Standby (ISB)
V _{HC} (3)	Χ	Χ	High-Z	Deselected — Standby (ISB1)

NOTES:

1. $H = V_{IH}$, $L = V_{IL}$, x = Don't care.

2. VLC = 0.2V, VHC = VCC -0.2V.

3. Other inputs \geq VHC or \leq VLC.

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade	Temperature	GND	Vcc
Commercial	0°C to +70°C	0V	4.5V to 5.5V
Industrial	-40°C to +85°C	0V	4.5V to 5.5V

3948 tbl 09

RECOMMENDED DC OPERATING **CONDITIONS**

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
VIH	Input High Voltage	2.2	_	Vcc+0.5	٧
VIL	Input Low Voltage	-0.5 ⁽¹⁾	_	0.8	V

NOTE:

2948 tbl 01 1. V_{IL} (min.) = -1.5V for pulse width less than 10ns, once per cycle.

2948 tbl 04

DC ELECTRICAL CHARACTERISTICS

 $Vcc = 5.0V \pm 10\%$

			IDT71256SA		
Symbol	Parameter	Test Condition	Min. Max.		Unit
ILI	Input Leakage Current	Vcc = Max., Vin = GND to Vcc	_ 5		μА
ILO	Output Leakage Current	$Vcc = Max., \overline{CS} = Vih, Vout = GND to Vcc$	_	5	μА
Vol	Output Low Voltage	IoL = 8mA, Vcc = Min.	_	0.4	V
Vон	Output High Voltage	IOH = -4mA, Vcc = Min.	2.4 —		V

2948 tbl 05

DC ELECTRICAL CHARACTERISTICS⁽¹⁾

 $(VCC = 5.0V \pm 10\%, VLC = 0.2V, VHC = VCC-0.2V)$

Symbol	Parameter	71256SA12 ⁽³⁾	71256SA15	71256SA20	71256SA25 ⁽³⁾	Unit
Icc	Dynamic Operating Current $\overline{CS} \le VIL$, Outputs Open, $VCC = Max.$, $f = fMAX^{(2)}$	160	150	145	145	mA
ISB	Standby Power Supply Current (TTL Level) $\overline{\text{CS}} \geq \text{ViH}$, Outputs Open, Vcc = Max., f = fMAX ⁽²⁾	50	40	40	40	mA
ISB1	Standby Power Supply Current (CMOS Level) $\overline{\text{CS}} \ge \text{Vhc}$, Outputs Open, $\text{Vcc} = \text{Max.}$, $\text{f} = 0^{(2)}$ $\text{Vin} \le \text{Vlc}$ or $\text{Vin} \ge \text{Vhc}$	15	15	15	15	mA

NOTES:

2948 tbl 06

- 1. All values are maximum guaranteed values.
- 2. fmax = 1/trc (all address inputs are cycling at fmax); f = 0 means no address input lines are changing .
- 3. Commercial temperature range only.

AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
AC Test Load	See Figures 1 and 2

2948 tbl 07

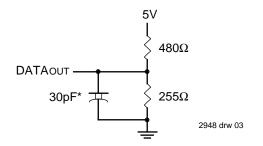
CAPACITANCE

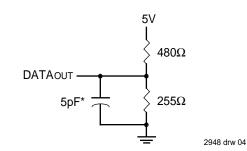
 $(TA = +25^{\circ}C, f = 1.0MHz, SOJ package)$

Symbol	Parameter ⁽¹⁾	Conditions	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	7	pF
CI/O	I/O Capacitance	Vout = 3dV	7	pF

NOTE:

2948 tbl 03





*Including jig and scope capacitance.

Figure 1. AC Test Load

Figure 2. AC Test Load (for tclz, tolz, tchz, tohz, tow, and twhz)

This parameter is guaranteed by device characterization, but not production tested.

AC ELECTRICAL CHARACTERISTICS (Vcc = $5.0V \pm 10\%$)

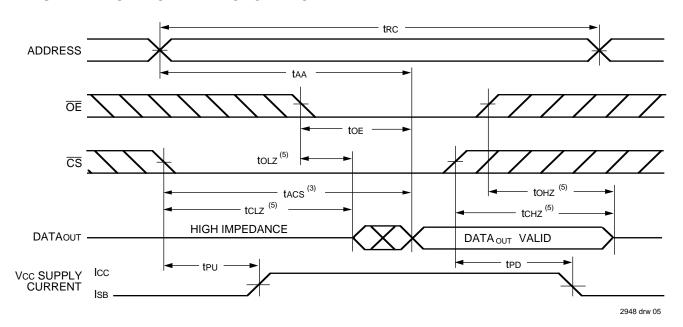
			SA12 ⁽²⁾	71256 71256		7125	6SA20	A20 71256S		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read Cyc	cle		•	-						
trc	Read Cycle Time	12	_	15	_	20		25		ns
tAA	Address Access Time	_	12	_	15	_	20	_	25	ns
tacs	Chip Select Access Time	_	12	_	15		20	_	25	ns
tcLZ ⁽¹⁾	Chip Select to Output in Low-Z	4	_	4	_	4	_	4	_	ns
tcHZ ⁽¹⁾	Chip Deselect to Output in High-Z	0	6	0	7	0	10	0	11	ns
toe	Output Enable to Output Valid	_	6	_	7		10	_	11	ns
toLZ ⁽¹⁾	Output Enable to Output in Low-Z	0	_	0	_	0	_	0	_	ns
toHz ⁽¹⁾	Output Disable to Output in High-Z	0	6	0	6	0	8	0	10	ns
tон	Output Hold from Address Change	3	_	3	_	3		3	_	ns
tPU ⁽¹⁾	Chip Select to Power Up Time	0	_	0	_	0	_	0	_	ns
tPD ⁽¹⁾	Chip Deselect to Power Down Time	_	12	_	15		20	_	25	ns
Write Cyc	cle	· ·	Į.							!
twc	Write Cycle Time	12	_	15	_	20	_	25	_	ns
taw	Address Valid to End of Write	9	_	10	_	15	_	20	_	ns
tcw	Chip Select to End of Write	9	_	10	_	15	_	20	_	ns
tas	Address Set-up Time	0	_	0	_	0	_	0	_	ns
twp	Write Pulse Width	9	_	10	_	15	_	20	_	ns
twr	Write Recovery Time	0	_	0	_	0	_	0	_	ns
tow	Data Valid to End of Write	6	_	7	_	11	_	13	_	ns
tDH	Data Hold Time	0	_	0	_	0	_	0	_	ns
tow ⁽¹⁾	Output Active from End of Write	4	_	4	_	4	_	4	_	ns
twHZ ⁽¹⁾	Write Enable to Output in High-Z	0	6	0	6	0	10	0	11	ns

NOTE:

1. This parameter is guaranteed with the AC Load (Figure 2) by device characterization, but is not production tested.

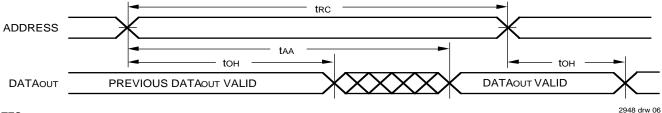
2. Commercial temperature range only.

TIMING WAVEFORM OF READ CYCLE NO. 1⁽¹⁾



2948 tbl 08

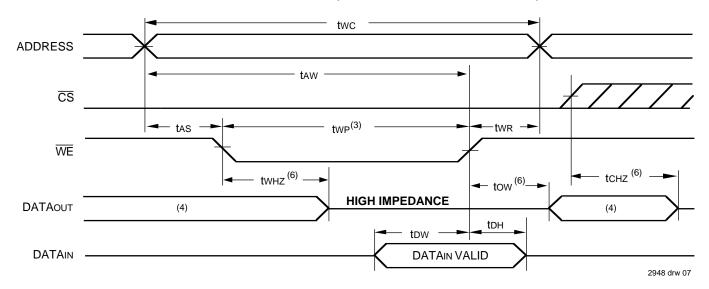
TIMING WAVEFORM OF READ CYCLE NO. $2^{(1,2,4)}$



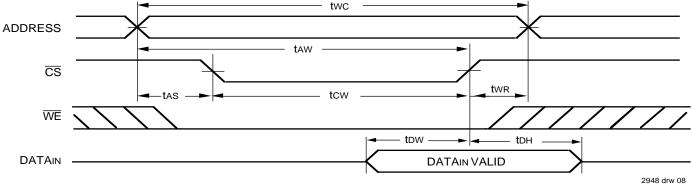
NOTES:

- 1. WE is HIGH for Read Cycle.
- 2. Device is continuously selected, \overline{CS} is LOW.
- 3. Address must be valid prior to or coincident with the later of $\overline{\text{CS}}$ transition LOW; otherwise tax is the limiting parameter.
- OE is LOW.
- 5. Transition is measured ±200mV from steady state.

TIMING WAVEFORM OF WRITE CYCLE NO.1 (WE CONTROLLED TIMING)(1,2,3,5)



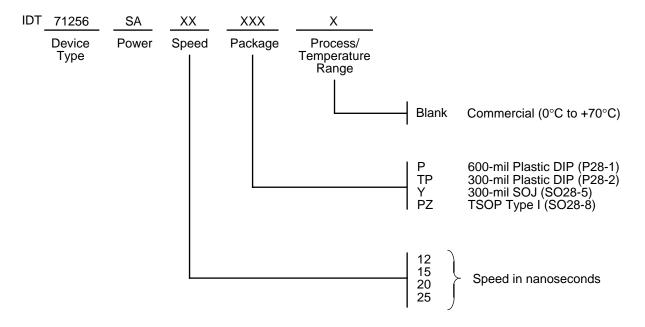
TIMING WAVEFORM OF WRITE CYCLE NO.2 (CS CONTROLLED TIMING)(1,2,5)



NOTES:

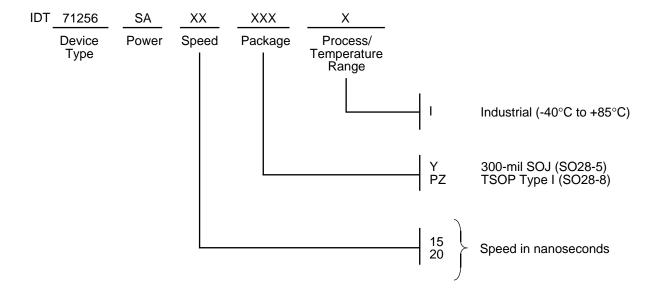
- 1. $\overline{\text{WE}}$ or $\overline{\text{CS}}$ must be HIGH during all address transitions.
- 2. A write occurs during the overlap of a LOW $\overline{\text{CS}}$ and a LOW $\overline{\text{WE}}$.
- 3. \overline{OE} is continuously \overline{HIGH} . If during a \overline{WE} controlled write cycle \overline{OE} is LOW, twp must be greater than or equal to twHz + tbW to allow the I/O drivers to turn off and data to be placed on the bus for the required tbW. If \overline{OE} is HIGH during a \overline{WE} controlled write cycle, this requirement does not apply and the minimum write pulse is as short as the specified twp.
- 4. During this period, I/O pins are in the output state, and input signals must not be applied.
- 5. If the CS LOW transition occurs simultaneously with or after the WE LOW transition, the outputs remain in a high-impedance state.
- 6. Transition is measured ±200mV from steady state.

ORDERING INFORMATION - COMMERCIAL



2948 drw 09

ORDERING INFORMATION - INDUSTRIAL



2948 drw 10